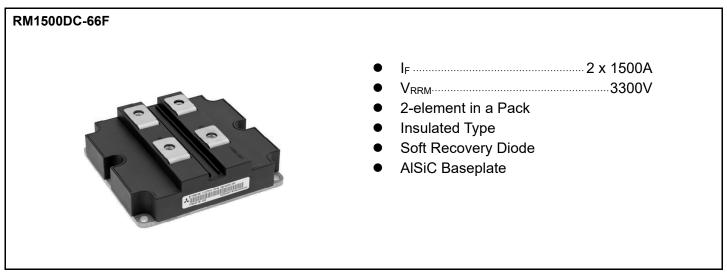


< HIGH VOLTAGE DIODE MODULES >

RM1500DC-66F

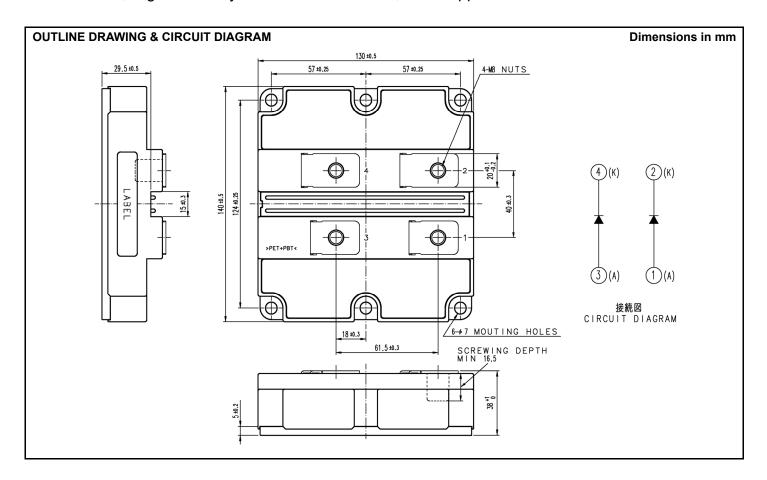
HIGH POWER SWITCHING USE INSULATED TYPE

High Voltage Diode Modules



APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers



HIGH POWER SWITCHING USE INSULATED TYPE

MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_j = -40+125$ °C	3300	V
		$T_j = -50$ °C	3200	V
I _F	Forward current	DC, T _c = 80°C	1500	Α
I _{FSM}	Surge (non-repetitive) forward current	T = 405°C + = 40 max Half sine ways V = 0.V	14.0	kA
l ² t	Surge current load integral	T_{j_start} = 125°C, t_p = 10 ms, Half-sine wave, V_R = 0 V	980	kA ² s
P _{tot}	Maximum power dissipation	T _c = 25°C	7800	W
V _{iso}	Isolation voltage	RMS, sinusoidal, f = 60 Hz, t = 1 min.	6000	V
V _e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60 Hz, Q _{PD} ≤ 10 pC	2600	V
Tj	Junction temperature		−50 ~ +150	°C
T _{jop}	Operating junction temperature		−50 ~ +150	°C
T _{stg}	Storage temperature		−55 ~ +150	°C

ELECTRICAL CHARACTERISTICS

Comple el	Item	Conditions		Limits			1.1
Symbol				Min	Тур	Max	Unit
·			$T_j = 25^{\circ}C$	_	_	2.0	
I_{RRM}	Repetitive reverse current	$V_{RM} = V_{RRM}$	T _j = 125°C	_	2.0	_	mA
			T _i = 150°C	_	12.0	_	
	Forward voltage	I _F = 1500 A	T _i = 25°C	_	2.20	_	V
V_{FM}			$T_{j} = 125^{\circ}C$	_	2.40	2.90	
			T _j = 150°C	-	2.35		
t _{rr}	Reverse recovery time		T _j = 25°C	_	0.65	_	μs
			T _j = 125°C	_	0.85	_	
		1000 1	T _j = 150°C	_	0.95	_	
	Reverse recovery current	$V_{CC} = 1800 \text{ V}$ $I_F = 1500 \text{ A}$	T _j = 25°C	_	1200	_	
I _{rr}		I _F = 1500 A	T _j = 125°C	_	1450	_	Α μC
		$-\mathbf{d}_{iF}/\mathbf{d}_{t} =$	T _j = 150°C	_	1500	_	
	Reverse recovery charge	" -	T _j = 25°C	_	1000	_	
Q_{rr}		5500 A/µs @ T _j = 25°C	T _j = 125°C	_	1650	_	
		5200 A/µs @ T _j = 125°C	T _j = 150°C	_	1950	_	
	Reverse recovery energy (Note 1)	5100 A/μs @ Τ _j = 150°C	T _i = 25°C	_	1.05 -	_	J
E _{rec(10%)}			T _j = 125°C	_	1.75		
		L _s = 100 nH	T _i = 150°C	_	2.00	_	
	Reverse recovery energy	Inductive load	T _j = 25°C	_	1.20	_	
E _{rec}			T _j = 125°C	_	2.00	_	J
			T _j = 150°C	_	2.30	_	

RM1500DC-66F HIGH POWER SWITCHING USE INSULATED TYPE

THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			l locit
		Conditions	Min Typ	Max	Unit	
R _{th(j-c)}	Thermal resistance	Junction to Case (per 1/2 module)	-		16.0	K/kW
R _{th(c-s)}	Contact thermal resistance	Case to heat sink, λ_{grease} = 1 W/m k $D_{(c-s)}$ = 100 µm (per 1/2 module)		17.5	_	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			I Incid
			Min	Тур	Max	Unit
M _t	Mounting torque	M8 : Main terminals screw	7.0	-	22.0	N·m
Ms		M6 : Mounting screw	3.0	_	6.0	N·m
m	Mass		1	8.0		kg
CTI	Comparative tracking index		600	1	1	_
d _a	Clearance		19.5	1		mm
d _s	Creepage distance		32.0	1		mm
L _{PAK}	Parasitic stray inductance	1/2 module	_	33.0	_	nΗ
R _{AA'+KK'}	Internal lead resistance	T _c = 25°C, 1/2 module	_	0.14	_	mΩ

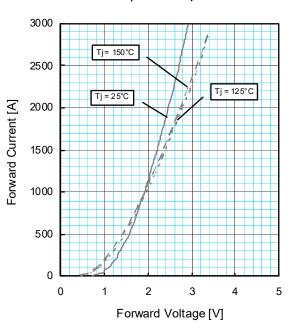
Note 1. $E_{rec(10\%)}$ is the integral of $0.1V_R \times 0.1I_F \times dt$.

HIGH POWER SWITCHING USE

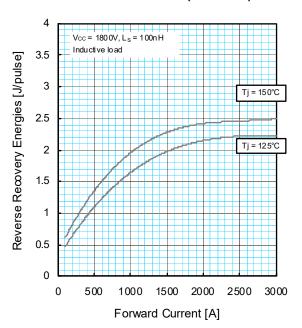
PERFORMANCE CURVES

INSULATED TYPE

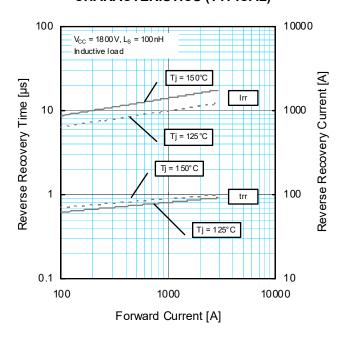
FORWARD CHARACTERISTICS (TYPICAL)



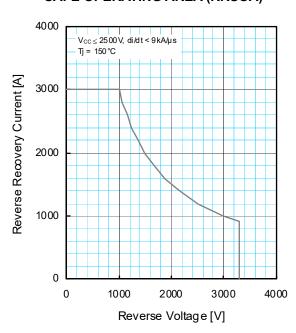
REVERSE RECOVERY ENERGY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY SAFE OPERATING AREA (RRSOA)

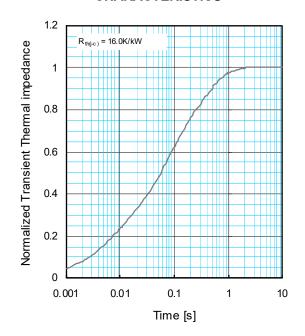


RM1500DC-66F

HIGH POWER SWITCHING USE INSULATED TYPE

PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^{n} R_{i} \left\{ I - exp^{\left(-\frac{t}{\tau_{i}}\right)} \right\}$$

$$\frac{1}{R_{i} [\text{K/kW}]:} \frac{2}{0.0096} \frac{3}{0.1893} \frac{4}{0.4044} \frac{1}{0.3967}$$

$$\tau_{i} [\text{sec}]: \frac{0.0001}{0.0058} \frac{0.0602}{0.0602} \frac{0.3512}{0.3512}$$

INSULATED TYPE

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INSULATED TYPE

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